BLF881; BLF881S

UHF power LDMOS transistor Rev. 4 — 1 September 2015

AMMPLEON

Product data sheet

Product profile 1.

1.1 General description

A 140 W LDMOS RF power transistor for broadcast transmitter applications and industrial applications. The transistor can deliver 140 W from HF to 1 GHz. The excellent ruggedness and broadband performance of this device makes it ideal for digital transmitter applications.

Typical performance Table 1.

RF performance at V_{DS} = 50 V in a common-source 860 MHz test circuit.

Mode of operation	f (MHz)		P _{L(PEP)} (W)	P _{L(AV)} (W)	•			
2-tone, class AB	f ₁ = 860; f ₂ = 860.1	-	140	-	21	49	-34	-
DVB-T (8k OFDM)	858	-	-	33	21	34	-	-33 <mark>[1]</mark>

^[1] Measured [dBc] with delta marker at 4.3 MHz from center frequency.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- 2-Tone performance at 860 MHz, a drain-source voltage V_{DS} of 50 V and a quiescent drain current $I_{Da} = 0.5 A$:
 - ◆ Peak envelope power load power = 140 W
 - Power gain = 21 dB
 - ◆ Drain efficiency = 49 %
 - ◆ Third order intermodulation distortion = -34 dBc
- DVB performance at 858 MHz, a drain-source voltage V_{DS} of 50 V and a quiescent drain current $I_{Dq} = 0.5 A$:
 - ◆ Average output power = 33 W
 - Power gain = 21 dB
 - ◆ Drain efficiency = 34 %
 - ◆ Shoulder distance = -33 dBc (4.3 MHz from center frequency)
- Integrated ESD protection
- Excellent ruggedness
- High power gain

- High efficiency
- Excellent reliability
- Easy power control
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- Communication transmitter applications in the UHF band
- Industrial applications in the UHF band

2. Pinning information

Table 2. Pinning

Table 2.	Pinning			
Pin	Description		Simplified outline	Graphic symbol
BLF881 (SOT467C)			
1	drain			,
2	gate			1
3	source	<u>[1]</u>		2
				3 sym112
				3,11112
BLF881S	(SOT467B)			
1	drain			
2	gate			1
3	source	<u>[1]</u>	-3	2
				3
				sym112

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	ackage					
	Name	Description	Version				
BLF881	-	flanged LDMOST ceramic package; 2 mounting holes; 2 leads	SOT467C				
BLF881S	-	earless LDMOST ceramic package; 2 leads	SOT467B				

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	104	V
V_{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Тур	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 80 ^{\circ}C;$ $P_{L(AV)} = 70 W$	[1]	0.95	K/W

^[1] $R_{th(j-c)}$ is measured under RF conditions.

6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.35 \text{ mA}$	<u>[1]</u>	104	-	-	V
V _{GS(th)}	gate-source threshold voltage	V_{DS} = 10 V; I_{D} = 135 mA	<u>[1]</u>	1.4	-	2.4	V
I _{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$		-	-	1.4	μА
I _{DSX}	drain cut-off current	$V_{GS} = V_{GSth} + 3.75 \text{ V}; V_{DS} = 10 \text{ V}$		19	21	-	Α
I _{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}$		-	-	140	nA
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GSth} + 3.75 \text{ V}; I_D = 4.5 \text{ A}$	<u>[1]</u>	-	210	-	$m\Omega$
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$		-	100	-	pF
Coss	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$		-	33.5	-	pF
C _{rss}	reverse transfer capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$		-	1	-	pF

^[1] I_D is the drain current.

Table 7. RF characteristics

 $T_h = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
2-Tone, cl	ass AB					
V_{DS}	drain-source voltage		-	50	-	V
I_{Dq}	quiescent drain current		-	0.5	-	Α
$P_{L(PEP)}$	peak envelope power load power		-	140	-	W
Gp	power gain		20	21	-	dB
η_{D}	drain efficiency		45	49	-	%
IMD3	third-order intermodulation distortion		-	-34	-30	dBc

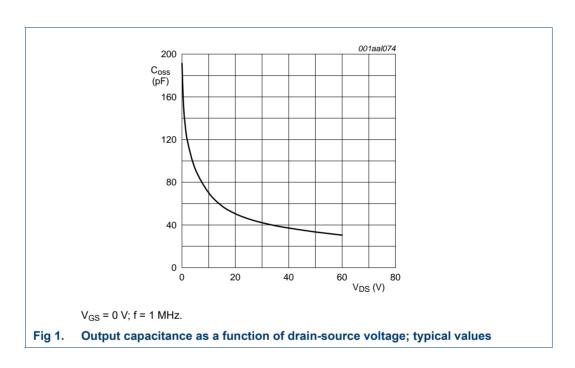
BLF881_BLF881S#4

Table 7. RF characteristics ...continued

 $T_h = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
DVB-T (8k	OFDM)					
V_{DS}	drain-source voltage		-	50	-	V
I_{Dq}	quiescent drain current		-	0.5	-	Α
$P_{L(AV)}$	average output power		-	33	-	W
Gp	power gain		20	21	-	dB
η_{D}	drain efficiency		30	34	-	%
IMD_{shldr}	intermodulation distortion shoulder		<u>[1]</u> _	-33	-30	dBc
PAR	peak-to-average ratio		[2]	8.3	-	dB

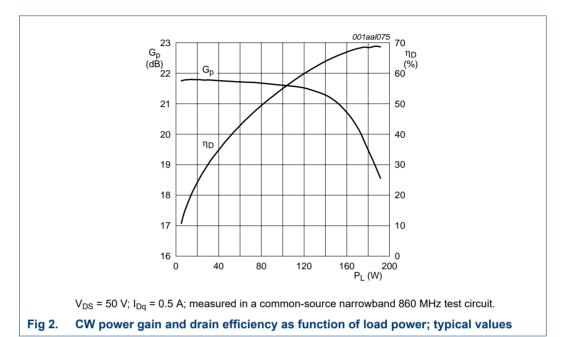
- [1] Measured [dBc] with delta marker at 4.3 MHz from center frequency.
- [2] PAR (of output signal) at 0.01 % probability on CCDF; PAR of input signal = 9.5 dB at 0.01 % probability on CCDF.



7. Application information

Narrowband RF figures

7.1.1 CW



7.1.2 2-Tone

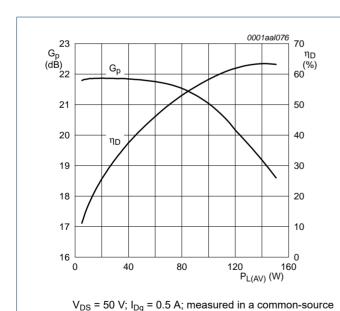
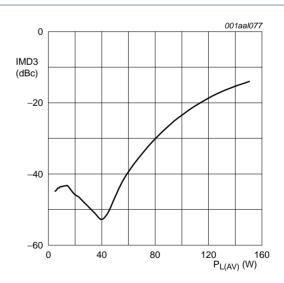


Fig 3. 2-Tone power gain and drain efficiency as function of average load power; typical values

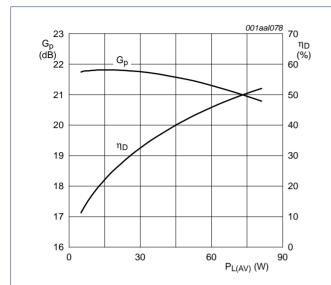
narrowband 860 MHz test circuit.



 V_{DS} = 50 V; I_{Dq} = 0.5 A; measured in a common-source narrowband 860 MHz test circuit.

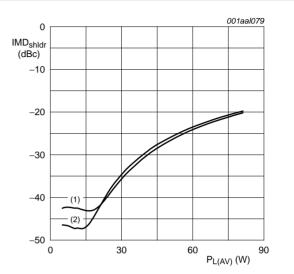
Fig 4. 2-Tone third order intermodulation distortion as a function of average load power; typical values

7.1.3 **DVB-T**



 V_{DS} = 50 V; I_{Dq} = 0.5 A; measured in a common-source narrowband 860 MHz test circuit.

Fig 5. DVB-T power gain and drain efficiency as function of average load power; typical values



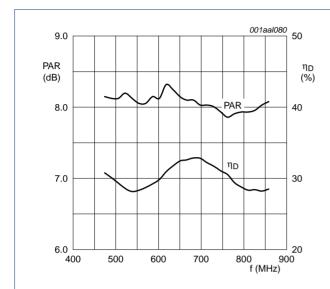
 V_{DS} = 50 V; I_{Dq} = 0.5 A; measured in a common-source narrowband 860 MHz test circuit.

- (1) Lower adjacent channel
- (2) Upper adjacent channel

Fig 6. DVB-T shoulder distance as a function of average load power; typical values

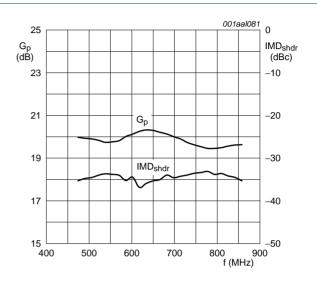
7.2 Broadband RF figures

7.2.1 DVB-T



 V_{DS} = 50 V; I_{Dq} = 0.35 A; $P_{L(AV)}$ = 33 W; measured in a common-source broadband test circuit as described in Section 8.

Fig 7. DVB-T PAR at 0.01 % probability on the CCDF and drain efficiency as function of frequency; typical values



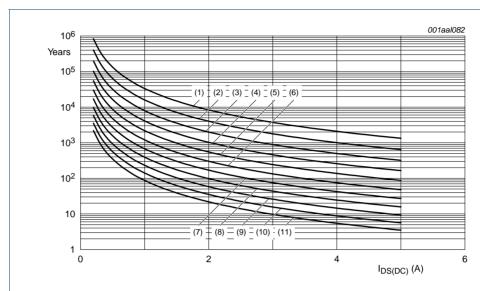
 V_{DS} = 50 V; I_{Dq} = 0.35 A; $P_{L(AV)}$ = 33 W; measured in a common-source broadband test circuit as described in Section 8.

Fig 8. DVB-T power gain and shoulder distance as function of frequency; typical values

7.3 Ruggedness in class-AB operation

The BLF881 and BLF881S are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 50 V; f = 860 MHz at rated power. Ruggedness is measured in the application circuit as described in Section 8.

7.4 Reliability



TTF (0.1 % failure fraction).

The reliability at pulsed conditions can be calculated as follows: TTF (0.1 %) \times 1 / δ .

- (1) $T_i = 100 \, ^{\circ}C$
- (2) $T_i = 110 \, ^{\circ}C$
- (3) $T_i = 120 \, ^{\circ}C$
- (4) $T_j = 130 \, ^{\circ}C$
- (5) $T_i = 140 \, ^{\circ}C$
- (6) $T_i = 150 \, ^{\circ}\text{C}$
- (7) $T_j = 160 \, ^{\circ}C$
- (8) $T_j = 170 \, ^{\circ}C$
- (9) $T_j = 180 \, ^{\circ}C$
- (10) $T_i = 190 \, ^{\circ}C$
- (11) $T_i = 200 \, ^{\circ}C$

Fig 9. BLF881 electromigration

8. Test information

Table 8. List of components

For test circuit, see Figure 10, Figure 11 and Figure 12.

Component	Description	Value		Remarks
C1, C2	multilayer ceramic chip capacitor	5.1 pF	[1]	
C3, C4	multilayer ceramic chip capacitor	10 pF	[2]	
C5	multilayer ceramic chip capacitor	6.8 pF	<u>[1]</u>	
C6	multilayer ceramic chip capacitor	4.7 pF	<u>[1]</u>	
C7	multilayer ceramic chip capacitor	2.7 pF	[1]	
C8, C9, C10, C25, C26	multilayer ceramic chip capacitor	100 pF	[1]	
C11, C27	multilayer ceramic chip capacitor	10 μF		TDK C570X7R1H106KT000N or capacitor of same quality.
C12	electrolytic capacitor	470 μF; 63 V		
C20	multilayer ceramic chip capacitor	10 pF	[3]	
C21	multilayer ceramic chip capacitor	8.2 pF	[3]	
C22	trimmer	0.6 pF to 4.5 pF		Tekelec
C23	multilayer ceramic chip capacitor	6.8 pF	[3]	
C24	multilayer ceramic chip capacitor	3.9 pF	[3]	
L1	stripline	-	[4]	(W \times L) 7 mm \times 15 mm
L2	stripline	-	[4]	(W \times L) 2.4 mm \times 9 mm
L3	stripline	-	[4]	(W \times L) 2.4 mm \times 10 mm
L4	stripline	-	[4]	(W \times L) 2.4 mm \times 25 mm
L5	stripline	-	[4]	(W \times L) 2.4 mm \times 10 mm
L6	stripline	-	[4]	(W \times L) 2.0 mm \times 20 mm
L7	stripline	-	[4]	(W \times L) 2.0 mm \times 21 mm
L20	stripline	-	[4]	(W \times L) 7 mm \times 12 mm
L21	stripline	-	[4]	(W \times L) 2.4 mm \times 13 mm
L22	stripline	-	[4]	(W \times L) 2.4 mm \times 31 mm
L23	stripline	-	[4]	(W \times L) 2.4 mm \times 5 mm
R1	resistor	100 Ω		
R2	resistor	10 kΩ		

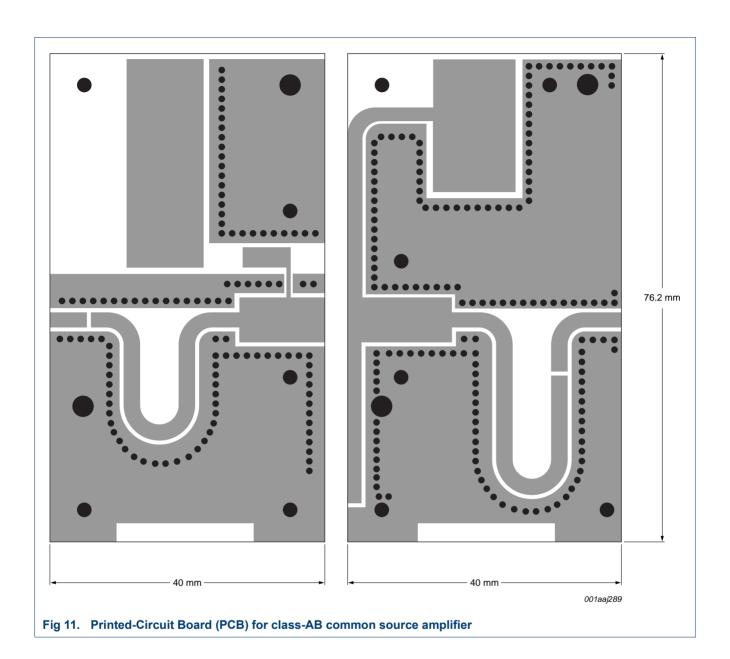
^[1] American technical ceramics type 100B or capacitor of same quality.

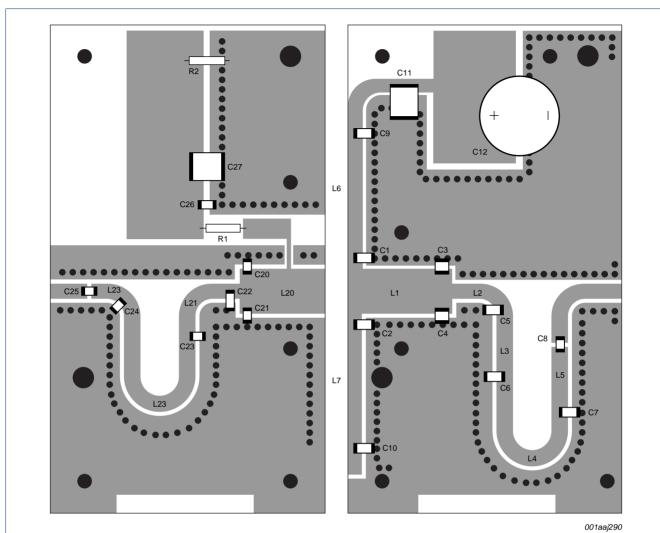
^[2] American technical ceramics type 180R or capacitor of same quality.

^[3] American technical ceramics type 100A or capacitor of same quality.

^[4] Printed-Circuit Board (PCB): Rogers 5880; ε_r = 2.2 F/m; height = 0.79 mm; Cu (top/bottom metallization); thickness copper plating = 35 μ m.

Product data sheet BLF881_BLF881S#4 C27 · V_{DD} All information provided in this document is subject to legal disclaimers C26 Rev. 4 — 1 September 2015 C20 C25 L21 L1 L22 L20 L2 L4 L3 -||-|C2 **‡** C24 C22 C21 **=** C5 H001aaj288 © Ampleon The Netherlands B.V. 2015. All rights reserved. 10 of 18 See Table 8 for a list of components. Fig 10. Class-AB common-source broadband amplifier





See <u>Table 8</u> for a list of components.

Fig 12. Component layout for class-AB common source amplifier

9. Package outline

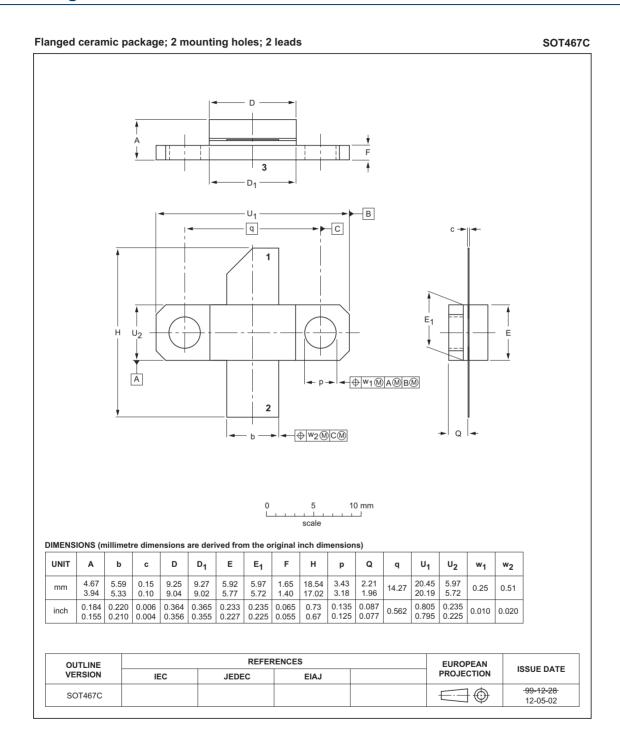


Fig 13. Package outline SOT467C

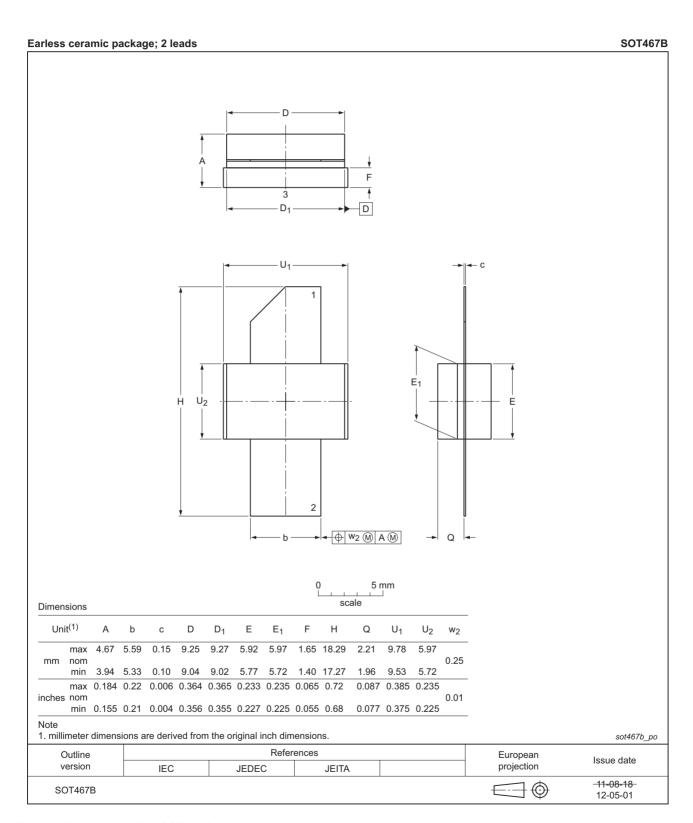


Fig 14. Package outline SOT467B

10. Abbreviations

Table 9. Abbreviations

Acronym	Description
CW	Continuous Wave
CCDF	Complementary Cumulative Distribution Function
DVB	Digital Video Broadcast
DVB-T	Digital Video Broadcast - Terrestrial
ESD	ElectroStatic Discharge
HF	High Frequency
IMD3	Third order InterModulation Distortion
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
OFDM	Orthogonal Frequency Division Multiplexing
PAR	Peak-to-Average power Ratio
PEP	Peak Envelope Power
RF	Radio Frequency
TTF	Time To Failure
UHF	Ultra High Frequency
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BLF881_BLF881S#4	20150901	Product data sheet	-	BLF881_BLF881S v.3		
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. Legal texts have been adapted to the new company name where appropriate. 					
BLF881_BLF881S v.3	20101207	Product data sheet	-	BLF881_BLF881S v.2		
BLF881_BLF881S v.2	20100210	Product data sheet	-	BLF881_BLF881S v.1		
BLF881_BLF881S v.1	20091210	Preliminary data sheet	-	-		

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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UHF power LDMOS transistor

14. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	2
2	Pinning information	2
3	Ordering information	2
4	Limiting values	3
5	Thermal characteristics	3
6	Characteristics	3
7	Application information	5
7.1	Narrowband RF figures	5
7.1.1	CW	5
7.1.2	2-Tone	5
7.1.3	DVB-T 6	ô
7.2	Broadband RF figures	7
7.2.1	DVB-T	7
7.3	Ruggedness in class-AB operation	7
7.4	Reliability	8
8	Test information	9
9	Package outline	3
10	Abbreviations1	5
11	Revision history	5
12	Legal information	6
12.1	Data sheet status	6
12.2	Definitions	6
12.3	Disclaimers	6
12.4	Licenses	7
12.5	Trademarks17	7
13	Contact information	7
11	Contents	0

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